

Impact of the Casimir-Polder Potential and Johnson Noise on Bose-Einstein Condensate Stability near Surfaces

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We investigate the stability of magnetically trapped atomic Bose-Einstein condensates and thermal clouds near the transition temperature at small distances $0.5 \text{ m} \leq d \leq 10 \text{ m}$ from a microfabricated silicon chip. For a 2 m thick copper film the trap lifetime is limited by Johnson-noise induced currents and falls below 1 s at a distance of 4 m . A dielectric surface does not adversely affect the sample until the attractive Casimir-Polder potential significantly reduces the trap depth.

Bose-Einstein condensates in magnetic traps [1, 2, 3, 4, 5] and waveguides [3, 6], and thermal atoms in waveguides [7] produced by microfabricated structures (microtraps) hold great promise for new quantum devices for atomic matter waves, such as Fabry-Pérot resonators [8], interferometers [9], or Josephson junctions [10]. Full quantum control over the motion of an ultracold atom of mass m and energy E requires potentials that vary abruptly on a length scale $\hbar/(mE)^{1/2} \sim 1 \text{ m}$. Such potentials can be created at small distances d from miniaturized field sources.

However, the proximity of a room-temperature surface can perturb the ultracold gas, and microtrap experiments have revealed condensate fragmentation [3, 4, 11], heating [1, 11], and reduced trap lifetime [11]. The fragmentation has been traced to spatial variations of the longitudinal magnetic field near a conductor carrying current [12], while heating and loss have been eliminated for distances $d \geq 70 \text{ m}$ by careful electronic design and shielding [4]. However, Jones et al. [13] and Harber et al. [14] have recently reported a fundamental limit due to spin flips induced by thermally excited currents in a mesoscopic conductor, in very good agreement with theoretical predictions [15] over the measurement regions $25 \text{ m} \leq d \leq 100 \text{ m}$ and $3 \text{ m} \leq d \leq 1 \text{ mm}$, respectively.

In this Letter, we explore fundamental limitations on condensate stability at small distances down to $d = 0.5 \text{ m}$ from dielectric and metal surfaces. For a 2 m thick copper film carrying no current we observe a distance-dependent lifetime $\tau(d)$ that is quantitatively explained by thermal magnetic field fluctuations arising from Johnson-noise induced currents [15, 16]. For the dielectric, we observe a reduction in trap lifetime only when the vicinity of the surface limits the trap depth. A one-dimensional (1D) evaporation model can explain the measured trap loss, but only when the attractive Casimir-Polder force [17] between atoms and surface is included. Our results suggest that the local manipulation of condensates will be possible using thin conductors, which have low magnetic field noise, on dielectric surfaces.

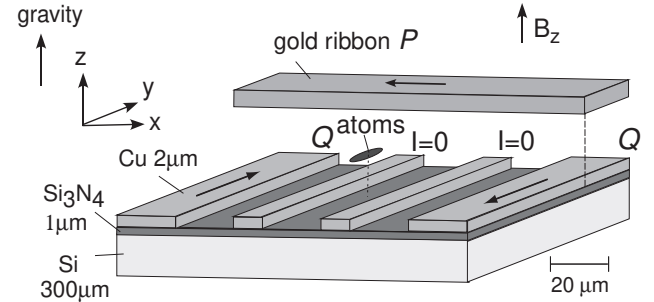


FIG. 1: Microfabricated chip. (Only the x direction is to scale.) The outer Cu wires (Q) generate a 2D quadrupole field in the xz plane. The ribbon (P) in combination with an external field gradient creates the confinement along y .

The atom-surface interactions are studied using ultracold atoms confined in a $\text{I} \otimes \text{e}$ Paul trap generated by currents flowing in microfabricated conductors on a silicon chip (see Fig. 1). The chip was produced by first coating a 300 m thick silicon substrate with a 1 m thick, electrically insulating Si_3N_4 diffusion barrier using plasma-enhanced chemical vapor deposition. Subsequently, a 20 nm thick Ti adhesion layer, a $2.15(20) \text{ m}$ thick Cu conducting layer, a 40 nm thick Ti, a 50 nm thick Pd, and a 100 nm thick Au layer were deposited by electron beam evaporation. Finally, the wires were defined by photolithography and wet etching.

The radial (xz) confinement of the $\text{I} \otimes \text{e}$ trap formed above the chip is provided by a 2D quadrupole field, generated by two copper wires Q along the y direction carrying antiparallel currents, in superposition with a bias field along z . The centers of the 2 m thick and 20 m wide Q wires are separated by 100 m . The axial (y) confinement is created by a current-carrying gold ribbon P along x in combination with an external field gradient along y . The 25 m thick, 150 m wide ribbon 155 m above the chip was wire-bonded to the surface.

The condensate production starts with a standard magneto-optical trap (MOT), into which typically 10^7 ^{87}Rb atoms are collected within 8 s from a Rb dispenser beam [2]. We then move the MOT cloud from the original distance $d = 17 \text{ mm}$ to within $d = 6 \text{ mm}$ of the chip surface, and compress it for 20 ms . After the MOT light has been extinguished, the atoms are optically pumped

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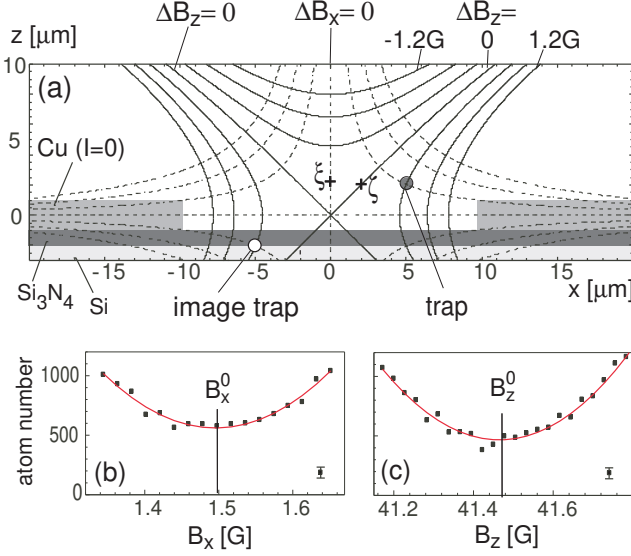


FIG. 2: (a) Map of relative field (B_x ; B_z) to trap position in the xz plane. Dashed (solid) lines are contours of B_x (B_z), plotted with 0.4 G spacing. (b,c) Measured atom loss versus B_x (B_z) near point (ξ^+) , marked by a cross.

in 400 μs into the $F = 2, m = 2$ ground state, and loaded into a large quadrupole trap with x, y, z gradients of 33, 8, and 25 G/cm, respectively. Next, by increasing a bias field B_z generated by a small coil located 2 mm below the chip, the atoms are compressed in 300 ms into a Ioffe microtrap, where the conversion from quadrupole to Ioffe trap geometry follows Ref. [18]. The trap is located at $d = 50$ μm from the surface and 430 μm away from the P ribbon along y for currents of 0.6 A in both the Q wires and the P ribbon. For a field at trap bottom of $B_0 = 1.5$ G, the radial and axial vibration frequencies are $\nu_{\text{rad}} = 2\pi \times 5.1$ kHz and $\nu_{\text{ax}} = 2\pi \times 70$ Hz, respectively. We typically load 3×10^6 atoms at an initial temperature of 300 K, peak density of $1.7 \times 10^{12} \text{ cm}^{-3}$, and peak collision rate of 140 s^{-1} . Three seconds of forced evaporation cool the sample to below the transition temperature $T_c = 0.8$ K. When the thermal component is no longer discernible in a time-of-flight image, the condensate contains 10^3 atoms at a peak density of $n_p = 8 \times 10^4 \text{ cm}^{-3}$. To measure surface-induced loss, we transport the condensate or a cloud near T_c adiabatically in 40 ms to a defined position near the surface, hold it there for a variable time, and image the cloud after moving it back to $d = 100$ μm . The noise-equivalent-optical-density of 1% in the absorption imaging corresponds to a small atom number noise $N = 50$ for a condensate. The procedure is repeated for each parameter value.

In order to compare an observed influence of the surface to theoretical models, the accurate calibration of the trap position (x, z) in the xz plane is crucial. While optical imaging fails close to the chip, the calibration is facilitated by the symmetry of the photolithographically defined Q wires (see Fig. 1). The trap is lo-

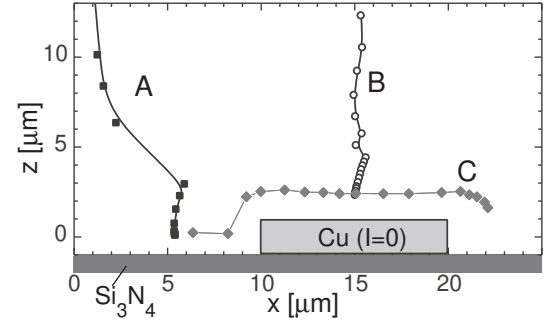


FIG. 3: Paths chosen for trap lifetime measurements above a dielectric surface (A) and above a copper film (B). Line C is the measured contour line of 22 ms lifetime near the metal.

cated where a homogeneous external bias field, with x and z components (B_x, B_z), cancels the field from the Q wires. Once the bias field value (B_x^0, B_z^0) that places the trap at the symmetry center ($x=0, z=0$) of the Q wires is known precisely, the atoms can be accurately positioned at arbitrary (x, z) by applying an additional field ($B_x; B_z$) = ($B_x - B_x^0; B_z - B_z^0$) to compensate the spatially varying field from the Q wires. Fig. 2a shows how the relative field (B_x, B_z) maps to trap position (x, z) . We also take into account a slight map distortion due to all other coils in the setup, which displaces the Ioffe trap by 0.50 (5) μm away from the chip compared to the map defined by the Q wires alone.

To precisely measure the symmetry-center bias field (B_x^0, B_z^0) that depends on unknown stray fields, we make use of the reflection symmetry of the Q wire configuration. We exploit the fact that a mirror image trap, located at $(-x, z)$, coexists with the trap at (x, z) (see Fig. 2a). As the trap and the image trap are brought close, the atoms can overcome the barrier between the traps, and will be lost if the image trap is inside the surface. Along a B_z contour, the loss is symmetric about the point $B_x = 0$ (e.g., point ξ^+ in Fig. 2a), where the minimum barrier leads to maximum loss. From the measured atom number versus B_x along the $B_z = -120$ mG contour, we determine B_x^0 with a precision of $B_x^0 = 4$ mG (Fig. 2b). Similarly, B_z^0 is determined within $B_z^0 = 10$ mG (Fig. 2c) by a measurement along the $B_x = 110$ mG contour near point ξ^- in Fig. 2a. In the spatial region of interest, the uncertainties ($B_x^0; B_z^0$) correspond to a trap z position error of 20 nm, small compared to a condensate size of 300 nm in the xz plane.

To verify that we can position the trap accurately relative to microscopic structures on the surface, we first measure a line of constant lifetime $\tau = 22$ ms near a Cu

film carrying no current, shown as curve C in Fig. 3. This "surface microscopy" yields a contour that displays the expected symmetry about the metal, which confirms the skewed field-to-position mapping in Fig. 2a. Fig. 3 also shows the trajectories we then use to measure the lifetime above the Si_3N_4 dielectric (A) and the copper film (B). Path A is selected to avoid coupling to the image

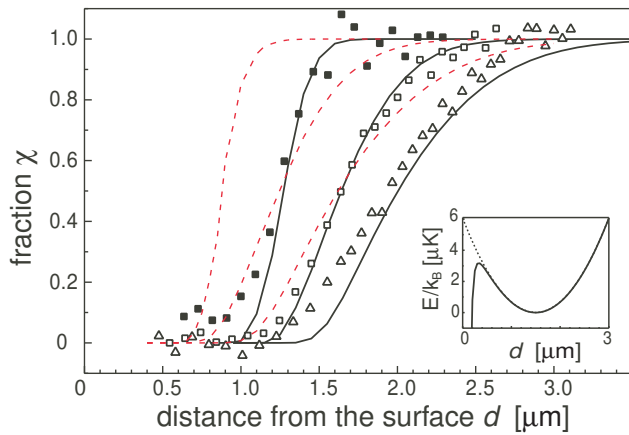


FIG. 5: Remaining atom fraction χ in a trap at distance d from dielectric surface for a condensate (solid squares), and for thermal clouds at 2.1 K (open squares) and 4.6 K (triangles). The solid (dashed) lines are calculated with (without) Casimir-Polder potential for the BEC, 2.1 K, 4.6 K clouds (left to right). The inset shows the trapping potentials for $C_4 = 8.2 \times 10^{-56} \text{ Jm}^4$ (solid line) and $C_4 = 0$ (dotted line).

accept $C_P(d)$. When we take these error sources into account, our measurements in combination with the 1D evaporation model imply a 66 % condence range for C_4 between $1.2 \times 10^{-56} \text{ Jm}^4$ and $41 \times 10^{-56} \text{ Jm}^4$, which in-

cludes the nominal value $C_4 = 8.2 \times 10^{-56} \text{ Jm}^4$. The good agreement between our data and the predicted C_4 without any adjustment of parameters suggests that the Casimir potential limits the trap depth, and consequently lifetime, at small distances $d \lesssim 2 \text{ μm}$ from the dielectric surface. The discrepancy at small fraction χ is probably due to our simple 1D evaporation model which breaks down for $\chi \ll 1$, and also ignores evaporation-induced temperature changes. Our data exclude $C_4 = 0$, even if we allow for the largest possible systematic error.

In conclusion, we have characterized the stability of magnetically trapped ultracold atoms at small distances from a copper film and a dielectric surface. The condensate is stable over the dielectric, and the spectral density of the thermal magnetic field near a metal film scales with metal thickness. Therefore it will be possible to bring a stable ultracold cloud sufficiently close to the surface for the trapping potential to be locally manipulated.

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Note added: The Casimir potential cannot explain the anomalously short lifetime at the smallest distance $d = 1.5 \text{ μm}$ above the metal (see Fig. 4 and the "surface microscopy" curve C in Fig. 3). One possible explanation is patch potentials from Rb atoms adsorbed on the metal, as recently reported by McGuirk et al. [23].

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